Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	54526	alumina with (substrate carrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:31
L2	79348	alumina with (substrate carrier layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:42
L3	63767	leadframe (lead adj frame)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:32
L4	9846196	(transistor (temperature adj5 element) device chip die fet mosfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:32
L5	89430	(hybrid composite) with (device ic (integrated adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:33
L6	90	1 and 2 and 3 and 4 and 5 and (aperture hole via hollow hollowed opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:38
L7	232188	(ceramic alumina) with (substrate carrier layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:42
L8	758864	(resistor (heat adj4 element))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 10:42

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	63767	leadframe (lead adj frame)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 04:49
L2	9101	1 with (aperture hole via hollow hollowed opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 04:50
L3	576	composite and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 06:03
L4	758864	(resistor (heat adj4 element))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 06:00
L5	390935	(transistor (temperature adj5 element) device chip die fet mosfet) same 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 06:02
L6	56196	composite with (device ic (integrated adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 06:04
L7	113	5 and 6 and 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 06:04